

Landolt-Börnstein Substance/Property Index

III/41: Semiconductors (revised and extended contents of the volumes III/17 and III/22)

Subvolume III/41A2: Impurities and defects in Group IV elements, IV-IV and III-V compounds

- [General Introduction](#)
- [Measurement methods](#)
- [Trends of impurity and defect properties](#)

List of substances

Group IV elements (Impurities and defects)

- [diamond \(C\)](#)
- [silicon \(Si\)](#)
- [germanium\(Ge\)](#)

IV-IV compounds

- [silicon carbide \(SiC\)](#)

III-V compounds

- | | |
|--|---|
| boron nitride (BN) | gallium phosphide (GaP) |
| boron phosphide (BP) | gallium arsenide (GaAs) |
| aluminum nitride (AlN) | gallium antimonide (GaSb) |
| aluminum arsenide (AlAs) | indium phosphide (InP) |
| aluminum antimonide (AlSb) | indium arsenide (InAs) |
| gallium nitride (GaN) | indium antimonide (InSb) |

Solid solutions between III-V compounds

- | | |
|--|--|
| GaAs_{1-x} P_x | Ga_{1-x} Al_x Sb |
| GaAs_{1-x} Sb_x | Ga_x In_{1-x} P |
| InAs_{1-x} P_x | Ga_{1-x} In_x As |
| Ga_{1-x} Al_x As | |

Quaternary alloys

- [Ga_x Al_{1-x} As_y Sb_{1-y}](#)
- [Ga_x In_{1-x} As_y P_{1-y}](#)
- [\(Ga_x Al_{1-x}\)_y In_{1-y} P](#)
- [\(Ga_x Al_{1-x}\)_y In_{1-y} As](#)

Aluminum arsenide (AlAs)

[back to top](#)

[deep defect states](#)

[shallow impurities and defects](#)

[vibrational modes of impurities](#)

Aluminum nitride (AlN)

[back to top](#)

[impurities and defects](#)

Aluminum antimonide (AlSb)

[back to top](#)

[deep impurities](#)

[shallow impurities](#)

[vibrational modes](#)

Boron nitride (BN)

[back to top](#)

[deep defect states in cubic boron nitride](#)

[impurities in cubic and hexagonal boron nitride](#)

Boron phosphide (BP)

[back to top](#)

[deep defect states](#)

Diamond (C)

[back to top](#)

[impurities and defects, general characterization](#)

[classification of diamond material by the nitrogen impurity properties](#)

[binding energies of impurity levels](#)

[nomenclature of defects](#)

[data for defects](#)

[paramagnetic centers, basic concepts](#)

[EPR spectra A1-A11](#)

[EPR spectra AB1-AB7](#)

[EPR spectra Boron, E1, G1, KUL1-7, KY1](#)

[EPR spectra L1, ME1, N1-7](#)

[EPR spectra NE1-9](#)

[EPR spectra NIRIM 1-NIRIM 8](#)

[EPR spectra NL1, NOC1-4, NOL, O1-4](#)

[EPR spectra OK1, P1-2, PA1](#)

[EPR spectra R1-R18](#)

[EPR spectra RM1, RO1, S1-4, TL1](#)

[EPR spectra W1-W44](#)

[further EPR spectra: Mu, Mu*, beta, V0 and others](#)

[g-values and linewidths of paramagnetic centers in CVD diamond](#)

Gallium aluminum arsenide (Ga(1-x)Al(x)As)

[back to top](#)

[deep defects](#)

[optical properties of deep defects](#)

[rare earth impurities](#)

[shallow impurities and defects](#)

[solubility and diffusion of impurities](#)

[transition metal impurities](#)

Gallium aluminum antimonide ($\text{Ga}_{1-x}\text{Al}_x\text{Sb}$)

[back to top](#)

[deep defect states](#)

Indium gallium aluminum arsenide ($(\text{Ga}_x\text{Al}_{1-x})_y\text{In}_{1-y}\text{As}$)

[back to top](#)

[deep defects](#)

Gallium aluminum indium phosphide ($(\text{Ga}_x\text{Al}_{1-x})_y\text{In}_{1-y}\text{P}$)

[back to top](#)

[deep defects](#)

Gallium indium arsenide ($\text{Ga}_{1-x}\text{In}_x\text{As}$)

[back to top](#)

[defect levels, optical properties of impurities](#)

[solubility and diffusion of impurities](#)

Gallium aluminum arsenide antimonide ($\text{Ga}_x\text{Al}_{1-x}\text{As}_y\text{Sb}_{1-y}$)

[back to top](#)

[deep defects](#)

Gallium indium arsenide phosphide ($\text{Ga}_x\text{In}_{1-x}\text{As}_y\text{P}_{1-y}$)

[back to top](#)

[impurities and defects](#)

Gallium indium phosphide ($\text{Ga}_x\text{In}_{1-x}\text{P}$)

[back to top](#)

[defect levels](#)

[rare earth impurities](#)

[transition metal impurities](#)

Gallium arsenide (GaAs)

[back to top](#)

[acceptor ground state binding energies](#)

[binding energy of residual donors](#)

[bound exciton lifetimes](#)

[bound exciton transition energies](#)

[calibration of local vibrational mode absorption lines](#)

[capture and emission data for transition metal impurities](#)

[diffusion of impurities and defects, general](#)

[diffusion of Zn in GaAs](#)

[electron traps \(cross section not known\)](#)

[electron traps \(directly measured carrier cross sections\)](#)

[electron traps induced by proton and heavy ion implantation](#)

[energy levels of transition metal impurities](#)

[energy splittings of excited acceptor states](#)

[ESR data for shallow defects](#)

[ESR, ENDOR, and ODMR data](#)

[excited states related to transition metal impurities](#)

[experimental results on the 0.67-0.68 eV photoluminescence band](#)

[experimental results on the 0.77-0.8 eV photoluminescence band](#)

[gallium vacancy](#)

[heavy doping effects](#)

[hole traps \(cross section not measured\)](#)

[hole traps \(directly measured cross sections\)](#)

[hole traps induced by proton and heavy ion implantation](#)

[impurity diffusion coefficients](#)

[intrinsic or unidentified deep defect states](#)

[low temperature grown GaAs](#)
[magnetic properties and ESR of transition metal impurities](#)
[magnetic properties of isolated, substitutional transition metal impurities](#)
[magnetic properties of transition metal complexes](#)
[optical bands related to the 78/203 meV acceptor](#)
[optical properties of deep defects, general remarks](#)
[optical properties of isolated transition metal impurities](#)
[optical properties of transition metal impurity complexes](#)
[optical transitions in absorption related to the EL2 defect](#)
[oxygen and hydrogen in GaAs](#)
[photoluminescence bands](#)
[photoluminescence in n- and p-type GaAs](#)
[photoluminescence of low temperature grown GaAs](#)
[properties of acceptor excited states](#)
[properties of fast-electron-irradiated GaAs](#)
[properties of plastically deformed GaAs](#)
[properties of rare earth impurities](#)
[radiation-induced deep defect states: electron traps induced by electron irradiation](#)
[radiation-induced deep defect states: hole traps induced by electron irradiation](#)
[self-diffusion coefficients](#)
[shallow acceptors: ground state binding energies, general remarks](#)
[shallow defects and impurity complexes: copper complexes](#)
[shallow defects and impurity complexes: the 1.5040-1.5110 eV photoluminescence lines](#)
[shallow donors: chemical shifts, photoconductivity measurements and photoluminescence](#)
[solubility of impurities](#)
[the EL2/As\(Ga\) defect](#)
[transition energies of highly excited acceptor states](#)
[vibrational modes of impurities and defects: hydrogen complexes](#)
[vibrational modes of impurities and defects: irradiation defects](#)
[vibrational modes of impurities and defects: isolated impurities](#)
[vibrational modes of impurities and defects: isotopic clusters](#)
[vibrational modes of impurities and defects: lithium complexes](#)
[vibrational modes of impurities and defects: substitutional impurity complexes](#)

Gallium arsenide phosphide ($\text{GaAs}_{(1-x)}\text{P}_x$)

[back to top](#)

[deep defect states](#)
[solubility and diffusion of impurities](#)
[transition metal impurities](#)

Gallium arsenide antimonide ($\text{GaAs}_{(1-x)}\text{Sb}_x$)

[back to top](#)

[deep defect states](#)

Gallium nitride (GaN)

[back to top](#)

[esr and odmr data on hexagonal GaN](#)
[luminescence peak energies](#)
[properties of bound excitons](#)
[properties of deep defect states](#)
[shallow impurities](#)
[solubility and diffusion of impurities](#)

Gallium phosphide (GaP)

[back to top](#)

[binding energies of acceptors relative to the valence band maximum](#)
[binding energies of donors](#)
[bound excitons, general remarks](#)
[deep defects, general remarks](#)
[defect levels associated with transition metal impurities: capture and emission data](#)
[defect levels associated with transition metal impurities: energy levels](#)
[deformation potential of impurity states](#)
[energies and capture cross sections of electron traps](#)
[energies and capture cross sections of hole traps](#)
[ESR and ENDOR data for shallow impurities](#)
[ESR data of shallow acceptors](#)
[ESR, ENDOR, and ODMR data: electron-irradiated GaP:Fe](#)
[ESR, ENDOR, and ODMR data: gallium vacancy](#)
[ESR, ENDOR, and ODMR data: phosphorus antisite P\(Ga\)P\(3\) Y](#)
[ESR, ENDOR, and ODMR data: phosphorus antisite P\(Ga\)P\(4\)](#)
[excited states of acceptors](#)
[excited states of defects associated with transition metal impurities](#)
[excited states of donors](#)
[excitons bound to isoelectronic substituents and other neutral centers, general remarks](#)
[irradiation effects in rare earths doped GaP](#)
[J-J coupling and crystal field splittings of bound excitons](#)
[localization energies and splitting of excitons bound to acceptors](#)
[localization energies and splitting of excitons bound to donors](#)
[localization energies of bound excitons](#)
[localization energies of multiple bound excitons](#)
[magnetic properties and ESR of isolated, substitutional transition metal impurities](#)
[magnetic properties and ESR of transition metal impurities complexes](#)
[nitrogen-related electron traps in GaP](#)
[optical properties of deep defects: luminescence bands](#)
[optical properties of deep defects: optical absorption bands](#)
[optical properties of isolated, substitutional transition metal impurities](#)
[optical properties related to transition metal complexes](#)
[properties of deep defect states induced by high energy irradiation](#)
[properties of electron and hole traps induced by proton irradiation](#)
[properties of rare earth impurities](#)
[scattering cross-sections \$\sigma\$ for the no-phonon creation of free excitons](#)
[shallow impurities, general remarks](#)
[solubility and diffusion of impurities](#)
[spin-orbit coupling in bound hole states](#)
[splittings of 1S donor ground states](#)
[transition lifetimes of bound excitons](#)
[vibrational modes of hydrogen paired with impurity atoms](#)
[vibrational modes of impurities and defects](#)
[vibrational modes of irradiation defects](#)
[vibrational modes of substitutional impurity complexes](#)

Gallium antimonide (GaSb)

[back to top](#)

[bound excitons](#)
[deep defects](#)
[deep states introduced by donors](#)
[diffusion of impurities and defects](#)

[hole and electron traps](#)
[radiation induced deep defect states](#)
[shallow impurities and defects](#)
[vibrational modes of impurities](#)

Germanium (Ge)

[back to top](#)

[solubility of impurities, general](#)
[distribution coefficient of impurities, general](#)
[solubility and segregation data of impurities: groups I-VIIIA](#)
[solubility and segregation data of impurities: groups IB-VIIIB](#)
[shallow donors binding energies](#)
[shallow donor transition energies](#)
[donor excited state binding energies](#)
[valley-orbit splittings of ground states of shallow donors](#)
[D-states binding energies \$E_D\$](#)
[ground state energies of group VI substitutional donors](#)
[shallow acceptors binding energies](#)
[shallow single acceptor transition energies](#)
[acceptor excited state binding energies](#)
[deep centers, general characterization](#)
[neutral double acceptor binding energies](#)
[double acceptor ground state splitting](#)
[singly ionized double acceptor binding energies](#)
[transition energies for neutral double acceptors](#)
[positively charged multiple acceptor binding energies](#)
[energy levels of group I substitutional triple acceptors and related complexes](#)
[energy levels of transition metal impurities](#)
[energy levels of defect centers](#)
[capture cross-sections of impurities](#)
[photoionization cross-sections of impurities](#)
[deformation potentials of impurities](#)
[luminescence of bound excitons](#)
[electron paramagnetic resonance data](#)
[energies of local vibrational modes](#)

Indium arsenide (InAs)

[back to top](#)

[deep defect states](#)
[impurity diffusion coefficients](#)
[magnetic properties of transition metal impurities](#)
[self-diffusion coefficients](#)
[shallow impurities](#)
[solubility of impurities](#)
[transition metal impurities](#)
[vibrational modes of impurities](#)

Indium arsenide phosphide (InAs(1-x)P(x))

[back to top](#)

[solubility and diffusion of impurities](#)

Indium phosphide (InP)

[back to top](#)

[1 MeV electron irradiation-induced hole traps, measured by DLTS](#)
[acceptor excited states](#)
[capture and emission data of transition metal impurities](#)
[data from photoconductivity measurements](#)
[data from photoluminescence \(I\)](#)
[data from photoluminescence \(II\)](#)
[deep impurities, general](#)
[deformation potentials for bound holes](#)
[diffusion of impurities and defects](#)
[energy levels of transition metal impurities](#)
[ESR and ENDOR data: the electron g-factor](#)
[ESR and ODMR data](#)
[excited states of transition metal impurities](#)
[exciton impurity transition lifetime](#)
[intrinsic or unidentified deep defect states](#)
[irradiation effects of rare earths impurities](#)
[magnetic properties and ESR of transition metal impurities](#)
[magnetic resonance of rare earths impurities](#)
[optical properties of transition metal impurities](#)
[photoluminescence and optical spectrometry of rare earth impurities](#)
[properties of acceptor impurities](#)
[properties of excitons bound to acceptors](#)
[properties of rare earth impurities](#)
[properties of the \(D\(+\)\)X exciton complex](#)
[radiation-induced deep defect states](#)
[shallow impurities and defects: general remarks](#)
[vibrational modes of isolated impurities](#)

Indium antimonide (InSb)

[back to top](#)

[binding energies of shallow impurities](#)
[bound excitons](#)
[deep impurities](#)
[diffusion coefficients of impurities](#)
[radiation-induced defect states](#)
[self-diffusion coefficients](#)
[transition metal impurities](#)
[vibrational modes of substitutional impurities](#)

Silicon (Si)

[back to top](#)

[paramagnetic centers, general remarks](#)
[paramagnetic centers: summary of crystallographic systems and pointgroups](#)
[paramagnetic centers: principal values and directions of the g-tensor](#)
[paramagnetic centers: symmetry-imposed constraints on the elements of the Cartesian g-tensor](#)
[paramagnetic centers: effective g-values](#)
[paramagnetic centers: degeneracies of the elements of the g-tensor](#)
[paramagnetic centers: number of resonances](#)
[paramagnetic centers: principal values and orientations of g-tensors of triclinic centers](#)
[paramagnetic centers: principal values and orientations of g-tensors of monoclinic-I centers](#)
[paramagnetic centers: principal values and orientations of g-tensors of monoclinic-II centers](#)
[paramagnetic centers: principal values of g-tensors of orthorhombic-I centers](#)

[paramagnetic centers: principal values of g-tensors of orthorhombic-II centers](#)
[paramagnetic centers: principal values of g-tensors of tetragonal centers](#)
[paramagnetic centers: principal values of g-tensors of trigonal centers](#)
[paramagnetic centers: principal values of g-tensors of cubic centers](#)
[vibrational modes of substitutional impurities](#)
[vibrational modes of substitutional impurity complexes](#)
[vibrational modes of oxygen in Si](#)
[vibrational modes: fine structure due to silicon isotopes on ¹⁶O \(i\) absorption](#)
[vibrational modes: experimental parameters of the O_i modes](#)
[vibrational modes of interstitial impurity complexes](#)
[vibrational modes due to irradiation defects, general](#)
[vibrational modes: hydrogen atoms and molecules](#)
[vibrational modes: hydrogen complexes with donor and acceptor dopants](#)
[vibrational modes due to hydrogen paired with metallic impurities](#)
[vibrational modes of hydrogen bonded to radiation damage defects](#)
[vibrational modes: defect concentrations derived from the strengths of local absorption lines](#)
[properties of oxygen-related defects and microdefects, classification of defects](#)
[point defects: vacancies and interstitials](#)
[point defects: equilibrium concentration and diffusivity for vacancies and interstitials](#)
[point defects: atomic size effects of impurities](#)
[point defects: solubility of impurities](#)
[point defects: diffusivity of impurities](#)
[point defects: oxidation effects](#)
[point defects: carbon and oxygen](#)
[point defects: other impurities](#)
[aggregation phenomena](#)
[precipitation](#)
[microdefects: self-point microdefects \(swirl defects\)](#)
[microdefects: oxygen-related microdefects](#)
[microdefects not related to oxygen](#)
[microdefects: oxidation-induced stacking faults](#)
[microdefects: gettering and denuded zones](#)
[solubility, segregation and distribution coefficients of impurities and defects, general](#)
[solubility data of impurities: group IA](#)
[solubility data of impurities: group IIA](#)
[solubility data of impurities: group IIIB including rare earth elements](#)
[solubility data of impurities: group IVB](#)
[solubility data of impurities: group VB](#)
[solubility data of impurities: group VIB](#)
[solubility data of impurities: group VIIB](#)
[solubility data of impurities: group VIII \(iron group\)](#)
[solubility data of impurities: group VIII \(cobalt group\)](#)
[solubility data of impurities: group VIII \(nickel group\)](#)
[solubility data of impurities: group IB](#)
[solubility data of impurities: group IIB](#)
[solubility data of impurities: group VIII \(group IIIA\)](#)
[solubility data of impurities and native point defects: group IVA](#)
[solubility data of impurities: group VA](#)
[solubility data of impurities: group VIA](#)
[solubility data of impurities: group VIIA](#)
[distribution coefficients at the melting point](#)
[ionization energies of impurity levels, general](#)

[ionization energies and structural information on impurities: A-center-As4-Vac](#)
[ionization energies and structural information on impurities: Au-Au-Vac](#)
[ionization energies and structural information on impurities: B-B-Zn](#)
[ionization energies and structural information on impurities: Be-Ce](#)
[ionization energies and structural information on impurities: Co-Cr-Zn](#)
[ionization energies and structural information on impurities: Cu-Fe-Zn](#)
[ionization energies and structural information on impurities: Ga-Ge](#)
[ionization energies and structural information on impurities: H-Hf](#)
[ionization energies and structural information on impurities: Hg-Mg](#)
[ionization energies and structural information on impurities: Mn-Ni](#)
[ionization energies and structural information on impurities: O-Pd-H](#)
[ionization energies and structural information on impurities: Pt-S-Vac](#)
[ionization energies and structural information on impurities: Sb-Te-Se](#)
[ionization energies and structural information on impurities: Th-Zr](#)
[ionization energies: pressure coefficients of impurity levels](#)
[capture coefficients and cross-sections of impurity levels, general](#)
[capture coefficients and capture cross-sections for impurities and defects](#)
[photoionization cross-sections of impurity levels](#)
[excited bound states of acceptors and donors: acceptors of group III impurities, general](#)
[excited bound states of acceptors and donors: group III acceptors and acceptor-X centers](#)
[binding energies of even parity excited states of acceptors](#)
[excited bound states of acceptors and donors: acceptors incorporating group II impurities](#)
[excited bound states of acceptors and donors: donors of group V impurities and Li, general](#)
[excited bound states of acceptors and donors: group V donors, Lii related donors, and Mgi](#)
[binding energies of even parity excited states of donors](#)
[excited bound states of acceptors and donors: donors of group VI impurities, general](#)
[binding energies of ground and selected excited states of S-, Se-, and Te-related centers](#)
[excited bound states of thermal donors \(TDs\): Oxygen-related defects, general](#)
[binding energies Ei and IR absorption line energies of neutral thermal donors \(TD0\)](#)
[binding energies Ei and IR absorption line energies of singly ionized thermal donors \(TD+\)](#)
[excited bound states of shallow thermal donors \(STDs\)](#)
[excited bound states of very shallow centers and deep transition metal defects](#)
[excited bound states: acceptors of group II impurities](#)
[excited bound states: pseudo-donors or pseudo-acceptors](#)
[photoluminescence properties of impurities and defects, general remarks](#)
[photoluminescence properties of excitons bound to neutral acceptors or donors](#)
[photoluminescence data for bound excitons](#)
[excitonic luminescence due to defects, mechanisms](#)
[photoluminescence data on defect spectra](#)
[photoluminescence data: supplementary data on optical defects](#)
[photoluminescence data: hydrogen-related optical defects](#)
[photoluminescence data: Er3+-related luminescence in silicon](#)
[photoluminescence spectroscopy using radioactive isotopes](#)
[further remarks to photoluminescence defect spectra](#)

Silicon carbide (SiC)

[back to top](#)

[defects in SiC](#)

[diffusion of impurities](#)

[energy levels and capture cross sections, defect centers not identified](#)

[energy levels and capture cross sections, identified defect centers](#)

[general characterization](#)

[impurities and defect levels, general](#)

[optical properties of impurities and other defects: acceptors Al, Ga, B and Be](#)

[optical properties of impurities and other defects associated with radiation damage, misc. defects](#)

[optical properties of impurities and other defects: hydrogen](#)

[optical properties of impurities and other defects: rare earth elements: erbium](#)

[optical properties of impurities and other defects: shallow donors](#)

[optical properties of impurities and other defects: transition metals](#)

[solubility of impurities](#)

[stacking order and number of inequivalent lattice sites in SiC](#)

Impurities and Defects in Group IV-IV and III-V
Compounds

Supplement to Vol. III/22b (Print Version), Revised and
Updated Edition of Vol. III/22b (CD-ROM)

2003, XXII, 334 p. 211 illus. With CD-ROM., Hardcover

ISBN: 978-3-540-43086-5